

20 V, P-channel Trench MOSFET 30 June 2016

Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-2.4	А
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2.4 A; T_j = 25 °C		-	97	128	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G G S 017aaa259

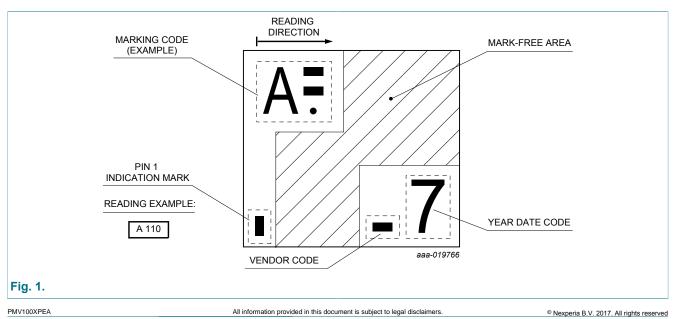
6. Ordering information

Table 3. Ordering information					
Type number Package					
	Name	Description	Version		
PMV100XPEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMV100XPEA	DP%

[1] % = placeholder for manufacturing site code



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8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

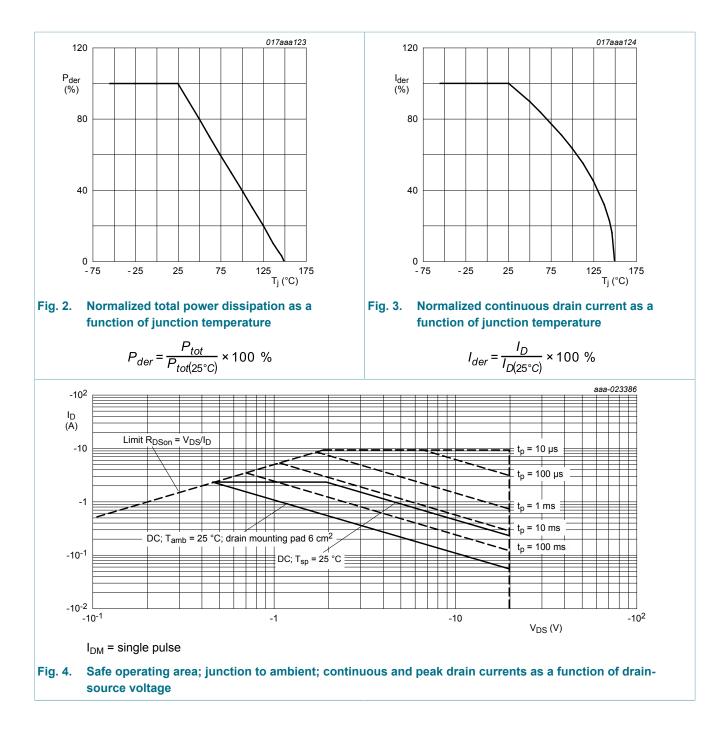
Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-2.4	А
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-1.5	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-10	А
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	T _{j(init)} = 25 °C; I _D = -0.5 A; DUT in avalanche (unclamped)		-	5	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	463	mW
			[1]	-	1.06	W
		T _{sp} = 25 °C		-	4.45	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode	·				
I _S	source current	T _{amb} = 25 °C	[1]	-	-1	А
ESD maxim	num rating					
V _{ESD}	electrostatic discharge voltage	HBM	[3]	-	2000	V
			1	1		1

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

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9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	226	270	K/W
	from junction to ambient		[2]	-	98	118	K/W

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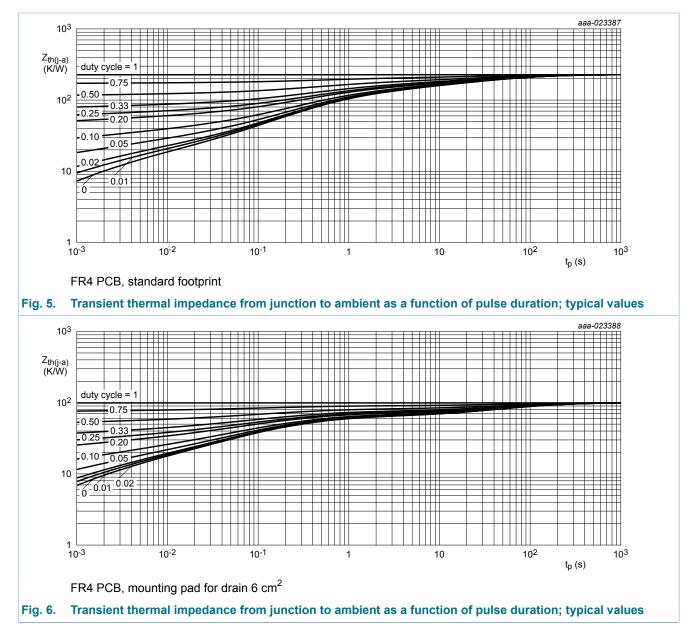
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	20	28	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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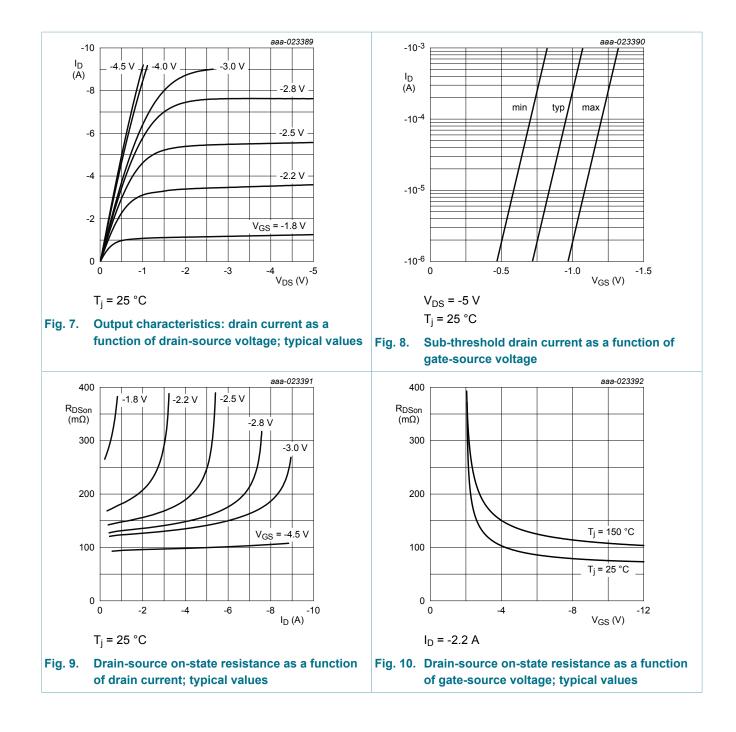
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = -250 μA; V _{GS} = 0 V; T _j = 25 °C	-20	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = -250 μA; V _{DS} =V _{GS} ; T _j = 25 °C	-0.75	-1	-1.25	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	2	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-2	μA
R _{DSon}	drain-source on-state	V _{GS} = -4.5 V; I _D = -2.4 A; T _j = 25 °C	-	97	128	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -2.4 A; T _j = 150 °C	-	142	187	mΩ
		V _{GS} = -2.5 V; I _D = -1.9 A; T _j = 25 °C	-	147	210	mΩ
9 _{fs}	forward transconductance	V _{DS} = -10 V; I _D = -2.4 A; T _j = 25 °C	-	6	-	S
R _G	gate resistance	f = 1 MHz	-	17.4	-	Ω
Dynamic ch	aracteristics	· · ·	I			
Q _{G(tot)}	total gate charge	V _{DS} = -10 V; I _D = -2.4 A; V _{GS} = -4.5 V;	-	3.4	6	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.85	-	nC
Q _{GD}	gate-drain charge		-	0.75	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	386	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	54	-	pF
C _{rss}	reverse transfer capacitance		-	40	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I _D = -2.4 A; V _{GS} = -4.5 V;	-	5	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t _{d(off)}	turn-off delay time		-	35	-	ns
t _f	fall time		-	17	-	ns
Source-drai	n diode		I		1	
V _{SD}	source-drain voltage	I _S = -1 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.7	-1.2	V

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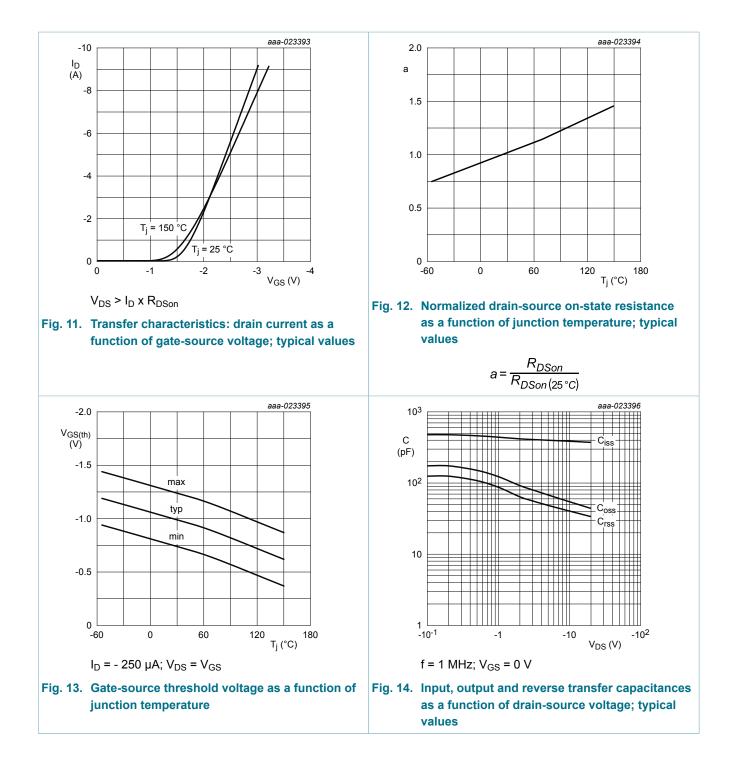


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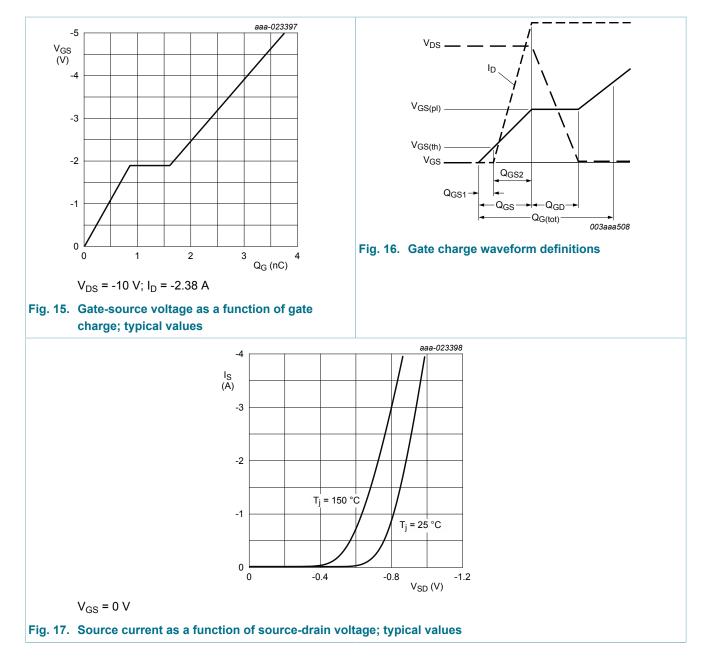
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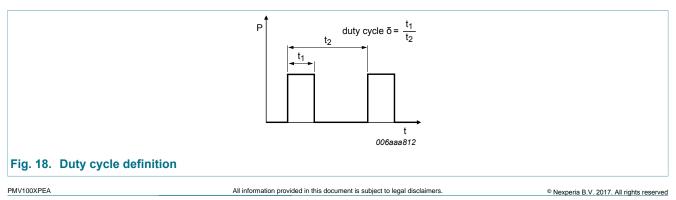
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11. Test information



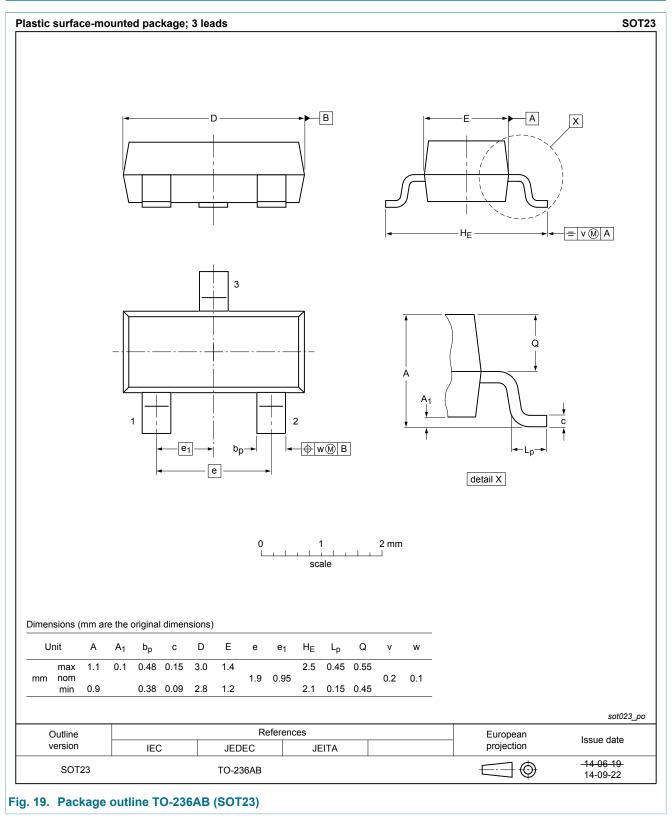
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11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

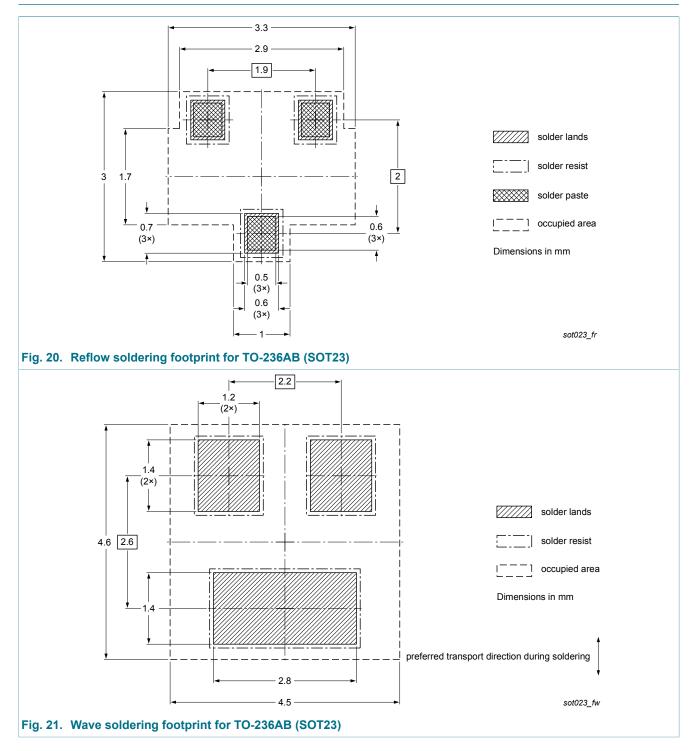
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMV100XPEA v.1	20160630	Product data sheet	-	-		

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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